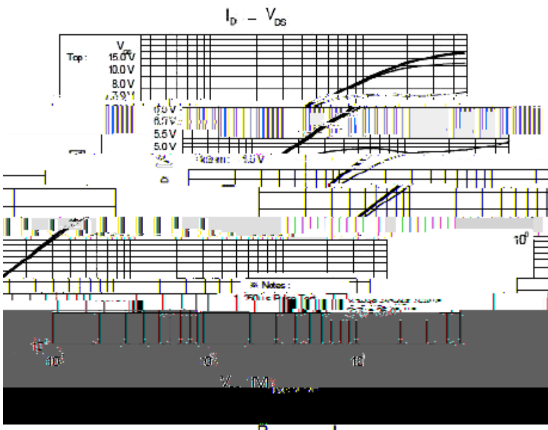
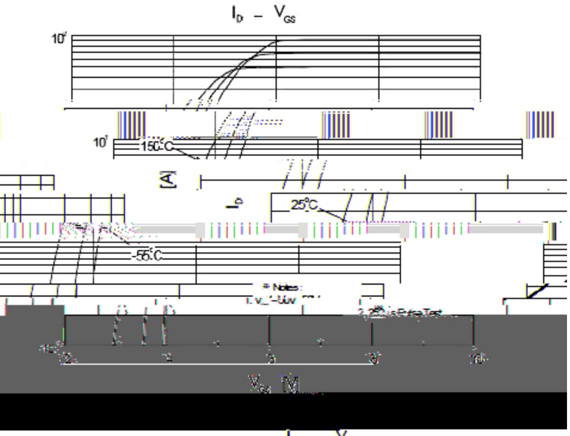
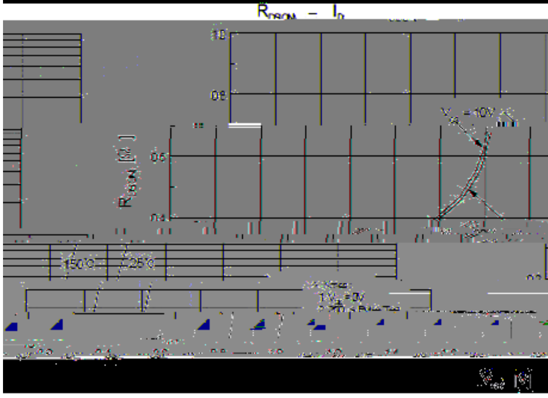
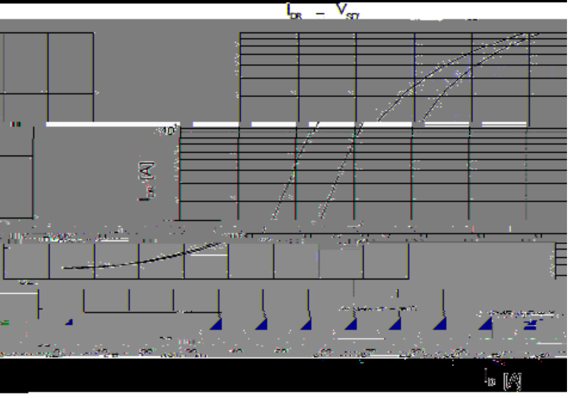
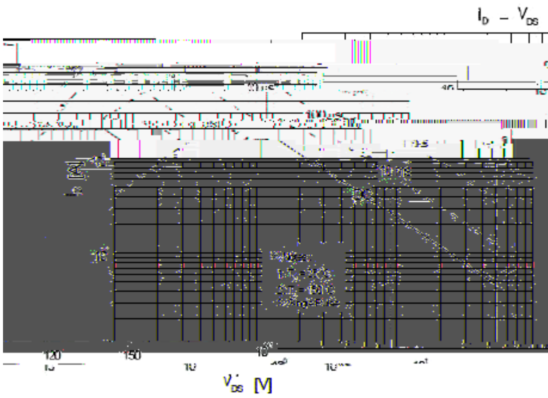
Parameter	Symbol	Rating	Unit
Drain-to-Source Breakdown Voltage	V_{DSS}	500	V
Continuous Drain Current	I_D(Tc=25)	20	A
Continuous Drain Current	I_D(Tc=100)	13	A
Drain Current Pulsed	I_{DP}	80	A
Gate-to-Source Voltage	V_{GSS}	±30	V
Repetitive Avalanche Energy	E_{AR}	28	mJ
Single Pulse Avalanche Energy	E_{AS}	1110	mJ
Peak Diode Recovery dv/dt	dv/dt	4.5	V/ns
Power Dissipation	P_D(Tc=25)	280	W
Junction Temperature Range	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

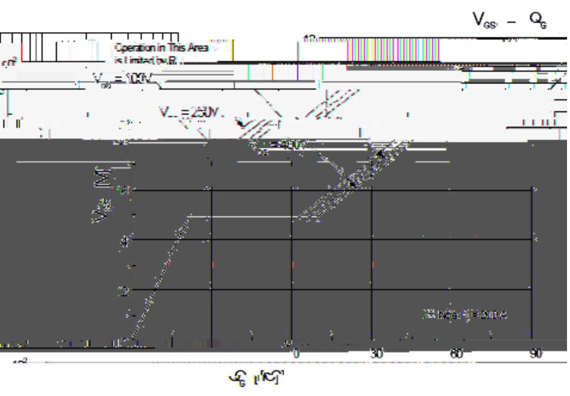

I_D – V_{DS}

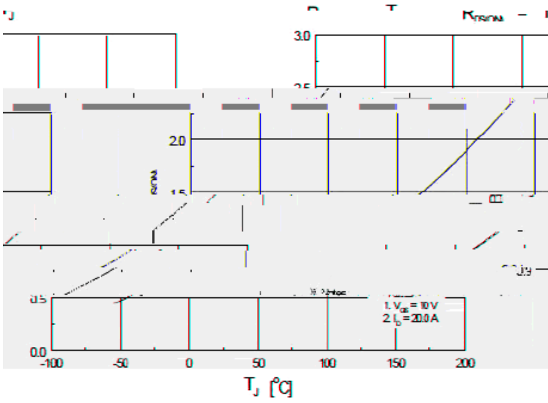

I_D – V_{GS}

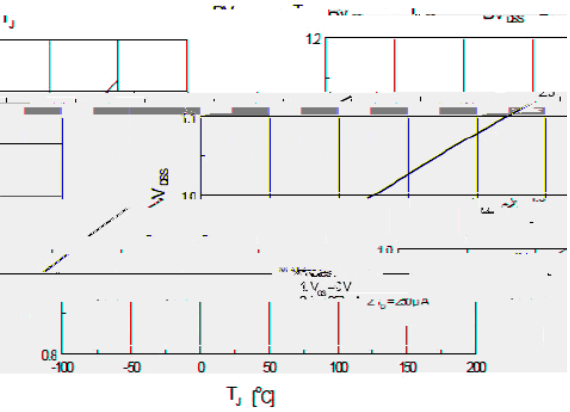

$R_{DS(ON)}$ – I_D

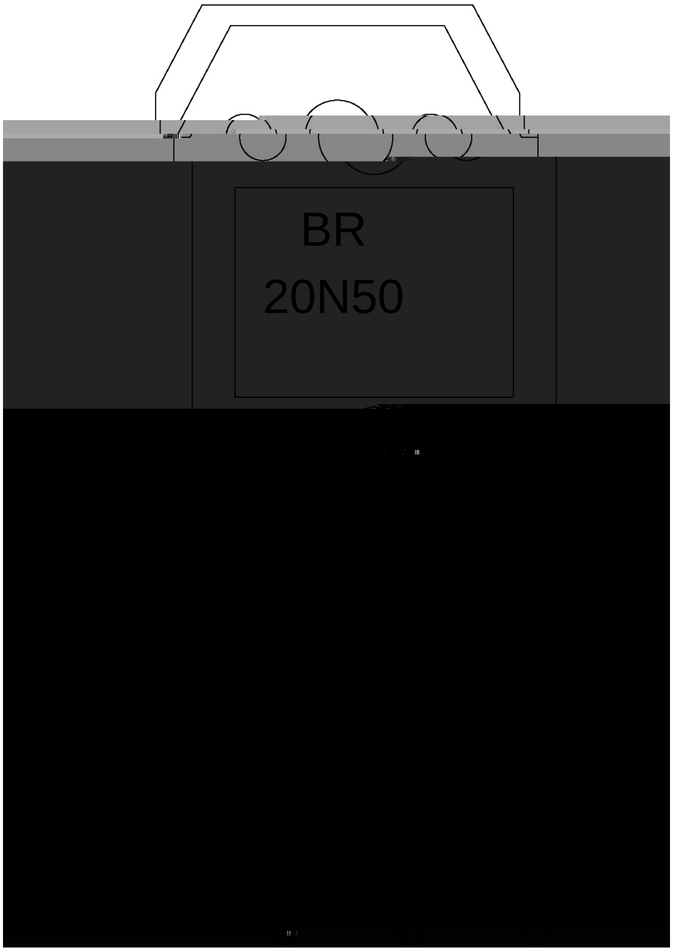

I_{DR} – V_{SD}


I_D – V_{DS}


V_{GS} – Q_G


$R_{DS(ON)}$ – T_J


BV_{DSS} – T_J



BR:

20N50

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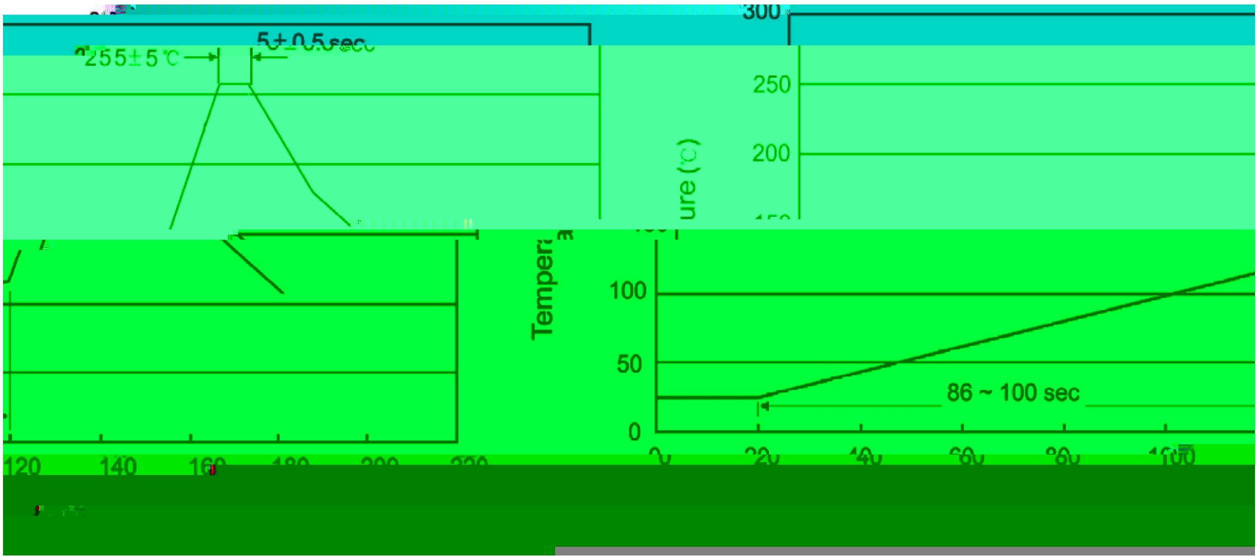
Note:

BR:	Company Code.
20N50:	Product Type.
****:	Lot No. Code, code change with Lot No.



Note:

1 25 150 60 90sec; 1.Preheating:25~150 , Time:60~90sec.

2 255±5 2534.98(2.Peak35340;)T53.7.00174 222: TD7(:)-3.1(25~1504ETj

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